

Dominique Vuillaume

List of Publications by Year in descending order

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229
papers

8,965
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57631

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236
all docs

236
docs citations

236
times ranked

8438
citing authors

#	ARTICLE	IF	CITATIONS
1	Nanoscale thermal conductivity of Kapton-derived carbonaceous materials. Journal of Applied Physics, 2022, 131, 065102.	1.1	5
2	Terphenylthiazole-based self-assembled monolayers on cobalt with high conductance photo-switching ratio for spintronics. Nanoscale, 2022, 14, 5725-5742.	2.8	2
3	Thermal and electrical cross-plane conductivity at the nanoscale in poly(3,4-ethylenedioxythiophene):trifluoromethanesulfonate thin films. Nanoscale, 2022, , .	2.8	4
4	Thermal conductivity of benzothieno-benzothiophene derivatives at the nanoscale. Nanoscale, 2021, 13, 3800-3807.	2.8	12
5	Conductance switching of azobenzene-based self-assembled monolayers on cobalt probed by UHV conductive-AFM. Nanoscale, 2021, 13, 6977-6990.	2.8	13
6	Photocurrent deviation from linearity in an organic photodetector due to limited hole transport layer conductivity. Organic Electronics, 2020, 76, 105450.	1.4	7
7	Long-range electron transport in Prussian blue analog nanocrystals. Nanoscale, 2020, 12, 20374-20385.	2.8	4
8	Conductance switching at the nanoscale of diarylethene derivative self-assembled monolayers on $\text{La}_{0.7}\text{Sr}_{0.3}\text{MnO}_3$. Nanoscale, 2020, 12, 8268-8276.	2.8	11
9	Electrical molecular switch addressed by chemical stimuli. Nanoscale, 2020, 12, 10127-10139.	2.8	14
10	Covalent Grafting of Polyoxometalate Hybrids onto Flat Silicon/Silicon Oxide: Insights from POMs Layers on Oxides. ACS Applied Materials & Interfaces, 2020, 12, 48109-48123.	4.0	12
11	Charge transport through redox active $[\text{H}_7\text{P}_8\text{W}_{48}\text{O}_{184}]^{33-}$ polyoxometalates self-assembled onto gold surfaces and gold nanodots. Nanoscale, 2019, 11, 1863-1878.	2.8	25
12	Physical mechanisms involved in the formation and operation of memory devices based on a monolayer of gold nanoparticle-polythiophene hybrid materials. Nanoscale Advances, 2019, 1, 2718-2726.	2.2	8
13	On a generic theory of the organic electrochemical transistor dynamics. Organic Electronics, 2019, 72, 39-49.	1.4	2
14	The non-ideal organic electrochemical transistors impedance. Organic Electronics, 2019, 71, 14-23.	1.4	10
15	Molecular Electronics: From Single Molecule to Large Area Devices. ChemPlusChem, 2019, 84, 1215-1221.	1.3	20
16	Electron Transport through Self-Assembled Monolayers of Tripeptides. Journal of Physical Chemistry C, 2019, 123, 9600-9608.	1.5	13
17	Electronic Properties of Organic Monolayers and Molecular Devices. , 2019, , 299-332.		0
18	The formation of polymer-dopant aggregates as a possible origin of limited doping efficiency at high dopant concentration. Organic Electronics, 2018, 53, 135-140.	1.4	38

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19	Cation discrimination in organic electrochemical transistors by dual frequency sensing. <i>Organic Electronics</i> , 2018, 57, 232-238.	1.4	24
20	Impact of unintentional oxygen doping on organic photodetectors. <i>Organic Electronics</i> , 2018, 54, 64-71.	1.4	10
21	Electrical detection of plasmon-induced isomerization in moleculeâ€“nanoparticle network devices. <i>Nanoscale</i> , 2018, 10, 23122-23130.	2.8	5
22	Nanodot-Molecule Junctions: Assessing Intermolecular Interactions and Electron Transport at Microwave Frequencies. , 2018, , .		0
23	Perspective: Organic electronic materials and devices for neuromorphic engineering. <i>Journal of Applied Physics</i> , 2018, 124, 151902.	1.1	41
24	Molecular signature of polyoxometalates in electron transport of silicon-based molecular junctions. <i>Nanoscale</i> , 2018, 10, 17156-17165.	2.8	37
25	Neuromorphic Timeâ€“Dependent Pattern Classification with Organic Electrochemical Transistor Arrays. <i>Advanced Electronic Materials</i> , 2018, 4, 1800166.	2.6	42
26	Lightâ€“Stimulatable Molecules/Nanoparticles Networks for Switchable Logical Functions and Reservoir Computing. <i>Advanced Functional Materials</i> , 2018, 28, 1801506.	7.8	14
27	Toward a better understanding of the doping mechanism involved in Mo(tfd-COCF3) ₃ doped PBDTTT-c. <i>Journal of Applied Physics</i> , 2018, 123, 225501.	1.1	5
28	Negative Differential Resistance, Memory, and Reconfigurable Logic Functions Based on Monolayer Devices Derived from Gold Nanoparticles Functionalized with Electropolymerizable TEDOT Units. <i>Journal of Physical Chemistry C</i> , 2017, 121, 10131-10139.	1.5	24
29	New Photomechanical Molecular Switch Based on a Linear Î€-Conjugated System. <i>Journal of Physical Chemistry C</i> , 2017, 121, 12416-12425.	1.5	15
30	Estimation of Î€â€“Î€ Electronic Couplings from Current Measurements. <i>Nano Letters</i> , 2017, 17, 3215-3224.	4.5	35
31	Probing Frontier Orbital Energies of {Co ₉ (P ₂ W ₁₅) ₃ } Polyoxometalate Clusters at Moleculeâ€“Metal and Moleculeâ€“Water Interfaces. <i>Journal of the American Chemical Society</i> , 2017, 139, 14501-14510.	6.6	30
32	Electron-transport polymeric gold nanoparticles memory device, artificial synapse for neuromorphic applications. <i>Organic Electronics</i> , 2017, 50, 499-506.	1.4	11
33	Liquidâ€“Gated Organic Electronic Devices Based on Highâ€“Performance Solutionâ€“Processed Molecular Semiconductor. <i>Advanced Electronic Materials</i> , 2017, 3, 1700159.	2.6	28
34	Concentric-electrode organic electrochemical transistors: case study for selective hydrazine sensing. <i>Journal of Physics: Conference Series</i> , 2017, 939, 012017.	0.3	2
35	Concentric-Electrode Organic Electrochemical Transistors: Case Study for Selective Hydrazine Sensing. <i>Sensors</i> , 2017, 17, 570.	2.1	12
36	Interplay of multiple synaptic plasticity features in filamentary memristive devices for neuromorphic computing. <i>Scientific Reports</i> , 2016, 6, 39216.	1.6	25

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37	P-doped organic semiconductor: Potential replacement for PEDOT:PSS in organic photodetectors. Applied Physics Letters, 2016, 109, .	1.5	21
38	Physical Study by Surface Characterizations of Sarin Sensor on the Basis of Chemically Functionalized Silicon Nanoribbon Field Effect Transistor. Journal of Physical Chemistry C, 2016, 120, 11180-11191.	1.5	11
39	Whole organic electronic synapses for dopamine detection. , 2016, , .		8
40	Electrolyte-gated organic synapse transistor interfaced with neurons. Organic Electronics, 2016, 38, 21-28.	1.4	69
41	High Mobility Flexible Amorphous IGZO Thin-Film Transistors with a Low Thermal Budget Ultra-Violet Pulsed Light Process. ACS Applied Materials & Interfaces, 2016, 8, 34513-34519.	4.0	67
42	A 17â€%GHz molecular rectifier. Nature Communications, 2016, 7, 12850.	5.8	86
43	Plasticity in memristive devices for spiking neural networks. Frontiers in Neuroscience, 2015, 9, 51.	1.4	188
44	Influence of Molecular Organization on the Electrical Characteristics of Î€-Conjugated Self-Assembled Monolayers. Journal of Physical Chemistry C, 2015, 119, 5703-5713.	1.5	14
45	Non-Arrhenius conduction due to the interface-trap-induced disorder in X-doped amorphous In-X-Zn oxides thin-film transistors. Journal of Applied Physics, 2015, 117, 055707.	1.1	2
46	Short-term to long-term plasticity transition in filamentary switching for memory applications. , 2015, , .		2
47	Filamentary Switching: Synaptic Plasticity through Device Volatility. ACS Nano, 2015, 9, 941-949.	7.3	183
48	Low voltage and time constant organic synapse-transistor. Organic Electronics, 2015, 21, 47-53.	1.4	40
49	High Conductance Ratio in Molecular Optical Switching of Functionalized Nanoparticle Self-Assembled Nanodevices. Journal of Physical Chemistry C, 2015, 119, 21173-21183.	1.5	15
50	On the mechanical and electronic properties of thiolated gold nanocrystals. Nanoscale, 2015, 7, 1809-1819.	2.8	23
51	High speed e-beam lithography for gold nanoarray fabrication and use in nanotechnology. Beilstein Journal of Nanotechnology, 2014, 5, 1918-1925.	1.5	21
52	Interface dipole: Effects on threshold voltage and mobility for both amorphous and poly-crystalline organic field effect transistors. Organic Electronics, 2014, 15, 729-737.	1.4	42
53	A simple and inexpensive technique for PDMS/silicon chip alignment with sub-1/4m precision. Analytical Methods, 2014, 6, 97-101.	1.3	17
54	Impact of dopant species on the interfacial trap density and mobility in amorphous In-X-Zn-O solution-processed thin-film transistors. Journal of Applied Physics, 2014, 115, .	1.1	26

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55	Water Electrolysis and Energy Harvesting with Zero-Dimensional Ion-Sensitive Field-Effect Transistors. <i>Nano Letters</i> , 2013, 13, 3903-3908.	4.5	18
56	Langmuir-Blodgett Films of Amphiphilic Thieno[3,4- <i>c</i>]pyrrole-4,6-dione-Based Alternating Copolymers. <i>Macromolecules</i> , 2013, 46, 6408-6418.	2.2	22
57	Establishment of a Derivatization Method To Quantify Thiol Function in Sulfur-Containing Plasma Polymer Films. <i>Langmuir</i> , 2013, 29, 13183-13189.	1.6	26
58	Bio-Inspired Stochastic Computing Using Binary CBRAM Synapses. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 2402-2409.	1.6	356
59	Integrating Multiple Resistive Memory Devices on a Single Carbon Nanotube. <i>Advanced Functional Materials</i> , 2013, 23, 5631-5637.	7.8	12
60	Addition of HfO ₂ interface layer for improved synaptic performance of phase change memory (PCM) devices. <i>Solid-State Electronics</i> , 2013, 79, 227-232.	0.8	17
61	A Crown-Ether Loop-Derivatized Oligothiophene Doubly Attached on Gold Surface as Cation-Binding Switchable Molecular Junction. <i>Advanced Materials</i> , 2013, 25, 427-431.	11.1	21
62	Synaptic electronics. <i>Nanotechnology</i> , 2013, 24, 380201-380201.	1.3	17
63	Pavlov's Dog Associative Learning Demonstrated on Synaptic-Like Organic Transistors. <i>Neural Computation</i> , 2013, 25, 549-566.	1.3	76
64	Impact of PCM resistance-drift in neuromorphic systems and drift-mitigation strategy. , 2013, , .		20
65	Physical aspects of low power synapses based on phase change memory devices. <i>Journal of Applied Physics</i> , 2012, 112, .	1.1	115
66	Reliability studies of pentacene based thin film transistors. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1435, 6.	0.1	0
67	Aspects of computing with locally connected networks. <i>AIP Conference Proceedings</i> , 2012, , .	0.3	4
68	Different types of phase separation in binary monolayers of long chain alkyltrichlorosilanes on silicon oxide. <i>RSC Advances</i> , 2012, 2, 3014.	1.7	2
69	CBRAM devices as binary synapses for low-power stochastic neuromorphic systems: Auditory (Cochlea) and visual (Retina) cognitive processing applications. , 2012, , .		100
70	Conductance Statistics from a Large Array of Sub-10 nm Molecular Junctions. <i>ACS Nano</i> , 2012, 6, 4639-4647.	7.3	44
71	Molecule/Electrode Interface Energetics in Molecular Junction: A Transition Voltage Spectroscopy Study. <i>Journal of Physical Chemistry C</i> , 2012, 116, 20722-20730.	1.5	56
72	Low frequency dielectric loss of metal/insulator/organic semiconductor junctions in ambient conditions. <i>Organic Electronics</i> , 2012, 13, 1916-1924.	1.4	4

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73	Interface Engineering of PCM for Improved Synaptic Performance in Neuromorphic Systems. , 2012, , .		12
74	Role of Hydration on the Electronic Transport through Molecular Junctions on Silicon. Journal of Physical Chemistry C, 2012, 116, 17753-17763.	1.5	13
75	Visual Pattern Extraction Using Energy-Efficient 1T-PCM Synapse \cdot Neuromorphic Architecture. IEEE Transactions on Electron Devices, 2012, 59, 2206-2214.	1.6	238
76	A Memristive Nanoparticle/Organic Hybrid Synapstor for Neuroinspired Computing. Advanced Functional Materials, 2012, 22, 609-616.	7.8	163
77	Impact of chain length, temperature, and humidity on the growth of long alkyltrichlorosilane self-assembled monolayers. Physical Chemistry Chemical Physics, 2011, 13, 2870-2879.	1.3	39
78	Chemical functionalization of electrodes for detection of gaseous nerve agents with carbon nanotube field-effect transistors. Chemical Communications, 2011, 47, 6048.	2.2	18
79	A silicon nanowire ion-sensitive field-effect transistor with elementary charge sensitivity. Applied Physics Letters, 2011, 98, .	1.5	68
80	Phase change memory for synaptic plasticity application in neuromorphic systems. , 2011, , .		16
81	Phase change memory as synapse for ultra-dense neuromorphic systems: Application to complex visual pattern extraction. , 2011, , .		185
82	New Chemically Functionalized Nanomaterials for Electrical Nerve Agents Sensors. Journal of Physics: Conference Series, 2011, 307, 012008.	0.3	1
83	Recent results on organic-based molecular memories. Current Applied Physics, 2011, 11, e49-e57.	1.1	16
84	Evaluation of a Gate Capacitance in the Sub-aF Range for a Chemical Field-Effect Transistor With a Si Nanowire Channel. IEEE Nanotechnology Magazine, 2011, 10, 1172-1179.	1.1	11
85	Large Array of Sub 10\AA Single \cdot Grain Au Nanodots for use in Nanotechnology. Small, 2011, 7, 2607-2613.	5.2	31
86	Thiolate Chemistry: A Powerful and Versatile Synthetic Tool for Immobilization/Functionalization of Oligothiophenes on a Gold Surface. Chemistry - A European Journal, 2011, 17, 5628-5640.	1.7	11
87	High Gain and Fast Detection of Warfare Agents Using Back-Gated Silicon-Nanowired MOSFETs. IEEE Electron Device Letters, 2011, 32, 976-978.	2.2	21
88	One-by-one trap activation in silicon nanowire transistors. Nature Communications, 2010, 1, 92.	5.8	74
89	Functional Model of a Nanoparticle Organic Memory Transistor for Use as a Spiking Synapse. IEEE Transactions on Electron Devices, 2010, 57, 3115-3122.	1.6	37
90	Molecular Nanoelectronics. Proceedings of the IEEE, 2010, 98, 2111-2123.	16.4	42

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91	An Organic Nanoparticle Transistor Behaving as a Biological Spiking Synapse. <i>Advanced Functional Materials</i> , 2010, 20, 330-337.	7.8	320
92	Two-Terminal Carbon Nanotube Programmable Devices for Adaptive Architectures. <i>Advanced Materials</i> , 2010, 22, 702-706.	11.1	95
93	Sub-ppm Detection of Nerve Agents Using Chemically Functionalized Silicon Nanoribbon Field-Effect Transistors. <i>Angewandte Chemie - International Edition</i> , 2010, 49, 4063-4066.	7.2	32
94	High-Speed Programming of Nanowire-Gated Carbon-Nanotube Memory Devices. <i>Small</i> , 2010, 6, 2659-2663.	5.2	8
95	Development of a functional model for the Nanoparticle-Organic Memory transistor. , 2010, , .		4
96	Molecular relaxation dynamics in organic monolayer junctions. <i>Physical Review B</i> , 2010, 82, .	1.1	10
97	Relaxation dynamics in covalently bonded organic monolayers on silicon. <i>Physical Review B</i> , 2010, 82, .	1.1	16
98	High On-Off Conductance Switching Ratio in Optically-Driven Self-Assembled Conjugated Molecular Systems. <i>ACS Nano</i> , 2010, 4, 2411-2421.	7.3	128
99	Synthesis and electrical properties of fullerene-based molecular junctions on silicon substrate. <i>Journal of Materials Chemistry</i> , 2010, 20, 2680.	6.7	15
100	Oligothiophene-derivatized azobenzene as immobilized photoswitchable conjugated systems. <i>Chemical Communications</i> , 2010, 46, 3657.	2.2	27
101	Self-assembled monolayers for electrode fabrication and efficient threshold voltage control of organic transistors with amorphous semiconductor layer. <i>Organic Electronics</i> , 2009, 10, 119-126.	1.4	40
102	Doping of poly(3-hexylthiophene) nanofibers: microscopic morphology and electrical properties. <i>EPJ Applied Physics</i> , 2009, 46, 12504.	0.3	2
103	Self-assembly of the 3-aminopropyltrimethoxysilane multilayers on Si and hysteretic current-voltage characteristics. <i>Applied Physics A: Materials Science and Processing</i> , 2008, 90, 581-589.	1.1	121
104	Electroactive Nanorods and Nanorings Designed by Supramolecular Association of Conjugated Oligomers. <i>Chemistry - A European Journal</i> , 2008, 14, 4201-4213.	1.7	26
105	Structural Control of the Horizontal Double Fixation of Oligothiophenes on Gold. <i>Chemistry - A European Journal</i> , 2008, 14, 6237-6246.	1.7	9
106	Electropolymerized Self-Assembled Monolayers of a 3,4-Ethylenedioxythiophene-Thiophene Hybrid System. <i>Advanced Functional Materials</i> , 2008, 18, 2163-2171.	7.8	32
107	Electronic structure of highly crystalline polyaniline by study of tunneling conduction in n-Si/self-assembled monolayer/polyaniline heterostructures. <i>Organic Electronics</i> , 2008, 9, 602-608.	1.4	8
108	Gate pulse electrical method to characterize hysteresis phenomena in organic field effect transistor. <i>Organic Electronics</i> , 2008, 9, 979-984.	1.4	24

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127	Deposition of TTF derivative on carboxyl terminated self-assembled monolayers. Applied Surface Science, 2005, 246, 392-396.	3.1	6
128	A Tunnel Current in Self-Assembled Monolayers of 3-Mercaptopropyltrimethoxysilane. Small, 2005, 1, 725-729.	5.2	53
129	Morphology-dependent electric transport in textured ultrathin Al films grown on Si. Journal of Applied Physics, 2005, 98, 026103.	1.1	5
130	Fowler-Nordheim tunnelling and electrically stressed breakdown of 3-mercaptopropyltrimethoxysilane self-assembled monolayers. Nanotechnology, 2005, 16, 3064-3068.	1.3	16
131	Aluminum, oxide, and silicon phonons by inelastic electron tunneling spectroscopy on metal-oxide-semiconductor tunnel junctions: Accurate determination and effect of electrical stress. Journal of Applied Physics, 2004, 96, 5042-5049.	1.1	17
132	Metal-organic-metal bistable memory devices. Applied Physics Letters, 2004, 85, 5763-5765.	1.5	172
133	Localization and delocalization of charges injected in DNA. Applied Physics Letters, 2004, 85, 2637-2639.	1.5	30
134	Ambipolar Charge Injection and Transport in a Single Pentacene Monolayer Island. Nano Letters, 2004, 4, 2145-2150.	4.5	62
135	Conductivity of DNA probed by conducting-atomic force microscopy: Effects of contact electrode, DNA structure, and surface interactions. Journal of Applied Physics, 2004, 96, 2927-2936.	1.1	51
136	1-octadecene monolayers on Si(111) hydrogen-terminated surfaces: Effect of substrate doping. Journal of Applied Physics, 2004, 96, 1529-1536.	1.1	96
137	Inelastic electron tunnelling spectroscopy in N-MOS junctions with ultra-thin gate oxide. Solid-State Electronics, 2003, 47, 1663-1668.	0.8	8
138	The metal/organic monolayer interface in molecular electronic devices. Microelectronic Engineering, 2003, 70, 539-550.	1.1	44
139	Molecular Rectifying Diodes from Self-Assembly on Silicon. Nano Letters, 2003, 3, 741-746.	4.5	157
140	Inelastic electron tunneling spectroscopy: Capabilities and limitations in metal-oxide-semiconductor devices. Journal of Applied Physics, 2002, 91, 5896-5901.	1.1	18
141	Nanometer-Scale Organic Thin Film Transistors from Self-Assembled Monolayers. Journal of Nanoscience and Nanotechnology, 2002, 2, 267-279.	0.9	22
142	Properties of electronic traps at silicon/1-octadecene interfaces. Applied Physics Letters, 2001, 78, 1288-1290.	1.5	55
143	Determination of the electrical properties of 2.5 nm thick silicon-based dielectric films: thermally grown SiO _x . Journal of Non-Crystalline Solids, 2001, 280, 69-77.	1.5	3
144	Analytical Model for Molecular-Scale Charge Transport. Journal of Physical Chemistry A, 2001, 105, 4702-4707.	1.1	51

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145	Determination of the electrical properties of ultrathin silicon-based dielectric films: thermally grown SiNx. Solid-State Electronics, 2001, 45, 1265-1270.	0.8	5
146	Theory of electrical rectification in a molecular monolayer. Physical Review B, 2001, 64, .	1.1	165
147	Determination of the electrical properties of thermally grown ultrathin nitride films. Microelectronics Reliability, 2000, 40, 589-592.	0.9	2
148	High anisotropic conductivity in organic insulator/semiconductor monolayer heterostructure. Applied Physics Letters, 2000, 76, 1339-1341.	1.5	35
149	Low-voltage, 30 nm channel length, organic transistors with a self-assembled monolayer as gate insulating films. Applied Physics Letters, 2000, 76, 1941-1943.	1.5	313
150	Dependence of interface-state generation on field polarity in metal-oxide-silicon devices of various thicknesses and technologies. Journal Physics D: Applied Physics, 1999, 32, 1435-1442.	1.3	9
151	Experimental study of the quasi-breakdown failure mechanism in 4.5 nm-thick SiO ₂ oxides. Microelectronics Reliability, 1999, 39, 165-169.	0.9	8
152	Electron Transfer through a Monolayer of Hexadecylquinolinium Tricyanoquinodimethanide. Langmuir, 1999, 15, 4011-4017.	1.6	94
153	Stress induced leakage currents in N-MOSFETs submitted to channel hot carrier injections. Journal of Non-Crystalline Solids, 1999, 245, 41-47.	1.5	12
154	Chapter 4 Hot carrier injections in SiO ₂ and related instabilities in submicrometer mosfets. Instabilities in Silicon Devices, 1999, , 265-339.	0.0	3
155	Electron traps created in gate oxides by Fowler-Nordheim injections. Microelectronics Reliability, 1998, 38, 227-231.	0.9	6
156	Hot-carrier injections in SiO ₂ . Microelectronics Reliability, 1998, 38, 7-22.	0.9	17
157	Observation of unimolecular electrical rectification in hexadecylquinolinium tricyanoquinodimethanide. Thin Solid Films, 1998, 327-329, 326-330.	0.8	22
158	HOT-CARRIER RELIABILITY IN n-MOSFETs USED AS PASS-TRANSISTORS. Microelectronics Reliability, 1998, 38, 539-544.	0.9	3
159	Nano-field effect transistor with an organic self-assembled monolayer as gate insulator. Applied Physics Letters, 1998, 73, 2681-2683.	1.5	125
160	Electronic structure of a heterostructure of an alkylsiloxane self-assembled monolayer on silicon. Physical Review B, 1998, 58, 16491-16498.	1.1	63
161	Electrical Rectification by a Molecule of Hexadecylquinolinium Tricyanoquinodimethanide. Materials Research Society Symposia Proceedings, 1997, 488, 335.	0.1	8
162	Performances of Sexithiophene Based Thin-Film Transistor Using Self-Assembled Monolayers. Materials Research Society Symposia Proceedings, 1997, 488, 407.	0.1	11

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163	Physical Characterization and Electrical Transport in End-Group Functionalized Self-Assembled Monolayers. Materials Research Society Symposia Proceedings, 1997, 488, 847.	0.1	0
164	Unimolecular Electrical Rectification in Hexadecylquinolinium Tricyanoquinodimethanide. Journal of the American Chemical Society, 1997, 119, 10455-10466.	6.6	617
165	Electrical properties of end-group functionalised Self-Assembled Monolayers. Microelectronic Engineering, 1997, 36, 119-122.	1.1	11
166	A coupled I(V) and charge-pumping analysis of Stress Induced Leakage Currents in 5nm-thick gate oxides. Microelectronic Engineering, 1997, 36, 141-144.	1.1	13
167	Influences of the different degradation mechanisms in AC-stressed p-MOSFET's during pass transistor operation. Microelectronic Engineering, 1997, 36, 305-308.	1.1	1
168	New insights on the charging and discharging of electron traps created by homogeneous electron injection in gate oxide. Microelectronic Engineering, 1997, 36, 309-312.	1.1	0
169	Stress field polarity effect on defects generation in thin silicon dioxide films. Thin Solid Films, 1997, 296, 106-109.	0.8	5
170	Analysis of the hot-carrier degradation of deep-submicrometer large-angle-tilt-implanted drain (LATID) MOSFETs. Solid-State Electronics, 1997, 41, 1293-1301.	0.8	10
171	Suppression of Charge Carrier Tunneling through Organic Self-Assembled Monolayers. Physical Review Letters, 1996, 76, 4797-4800.	2.9	281
172	Organic insulating films of nanometer thicknesses. Applied Physics Letters, 1996, 69, 1646-1648.	1.5	113
173	Organic Insulating Films at Nanometer Scale. Materials Research Society Symposia Proceedings, 1996, 446, 79.	0.1	6
174	Improved Reliability With a New Plasma NH_3 Process for $0.35\mu m$ P+ Poly-Gate Nitrided Oxide P-Mosfet's. Materials Research Society Symposia Proceedings, 1996, 446, 91.	0.1	1
175	Comment on "hot-hole-induced negative oxide charges in n-MOSFETs" [with reply]. IEEE Transactions on Electron Devices, 1996, 43, 1473-1477.	1.6	5
176	Relaxation of the space charge created by Fowler-Nordheim injections in metal-oxide-semiconductor capacitors. Journal of Applied Physics, 1996, 80, 5469-5477.	1.1	4
177	A modified method of side data analysis of deep level transient spectroscopy spectra. Journal of Applied Physics, 1996, 79, 1468-1475.	1.1	0
178	Lifetime prediction methods for p-MOSFET's: a comparative study of standard and charge-pumping lifetime criteria. IEEE Transactions on Electron Devices, 1995, 42, 101-108.	1.6	10
179	Ultra-low conductivity through insulating self-assembled organic monolayers. Microelectronic Engineering, 1995, 28, 217-220.	1.1	10
180	Improved hot-carrier immunity of p-MOSFET's with 8nm thick nitrided gate-oxide during bi-directional stressing. Microelectronic Engineering, 1995, 28, 273-276.	1.1	2

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181	Experiments and modelling to determine trapped holes and slow states in Fowler-Nordheim stressed MOS capacitors. <i>Microelectronic Engineering</i> , 1995, 28, 329-332.	1.1	5
182	Interface state measurements by the DLS lock-in spectrometer. <i>Review of Scientific Instruments</i> , 1995, 66, 4283-4288.	0.6	5
183	Damage induced by carrier injection in 8 nm thick oxides and nitrided oxides. <i>Journal of Non-Crystalline Solids</i> , 1995, 187, 365-368.	1.5	0
184	Spin Dependent Recombination: An Improved Theory Applied to Deep Centers in Silicon. <i>Materials Science Forum</i> , 1994, 143-147, 1359-1364.	0.3	6
185	Electrical Characterization of Surface Defects on Porous p-Type Silicon. <i>Materials Science Forum</i> , 1994, 143-147, 1475-1480.	0.3	1
186	Temperature dependent study of spin dependent recombination at silicon dangling bonds. <i>Applied Physics Letters</i> , 1994, 64, 1690-1692.	1.5	17
187	Influence of surface defects on the electrical behavior of aluminum porous silicon junctions. <i>Applied Physics Letters</i> , 1994, 64, 2827-2829.	1.5	35
188	Alkyl-trichlorosilane monolayer as ultra-thin insulating film for silicon MIS devices. <i>Microelectronic Engineering</i> , 1993, 22, 101-104.	1.1	4
189	An improved theory of spin dependent recombination : application to the Pb center at the Si-SiO ₂ interface. <i>Microelectronic Engineering</i> , 1993, 22, 143-146.	1.1	8
190	The nature of interface states generated by high field injection. <i>Microelectronic Engineering</i> , 1993, 22, 201-206.	1.1	3
191	Models for the Si-SiO ₂ interface degradation at low injected electron fluences. <i>Microelectronics Journal</i> , 1993, 24, 361-369.	1.1	4
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